



# YJD27G10A

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## N-Channel Enhancement Mode Field Effect Transistor

### Product Summary

$V_{DS}$	100V
$I_D$	27A
$R_{DS(ON)}$ ( at $V_{GS}=10V$ )	29m
$R_{DS(ON)}$ ( at $V_{GS}=4.5V$ )	47m
100% EAS Tested	
100% $V_{DS}$ Tested	



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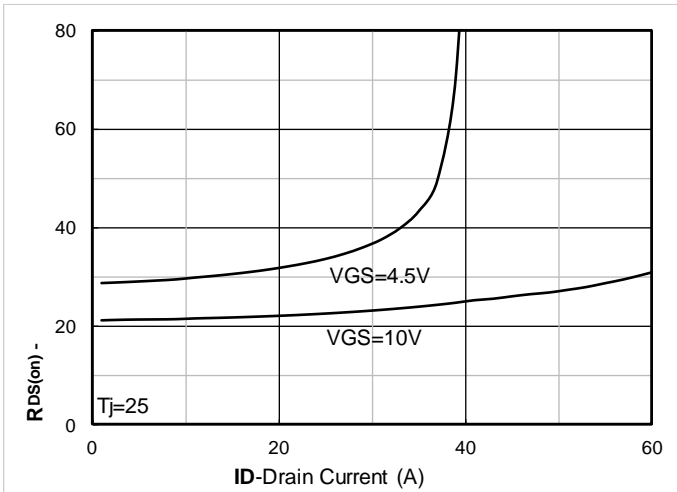


Figure 7. RDS(on) VS Drain Current

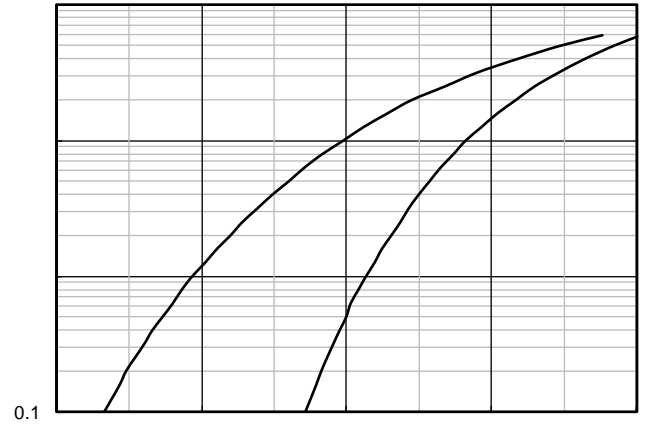


Figure 8. Forward characteristics of reverse diode

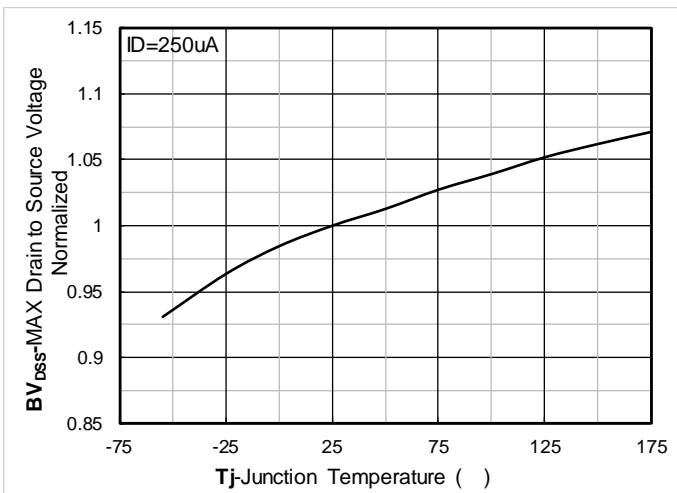


Figure 9. Normalized breakdown voltage

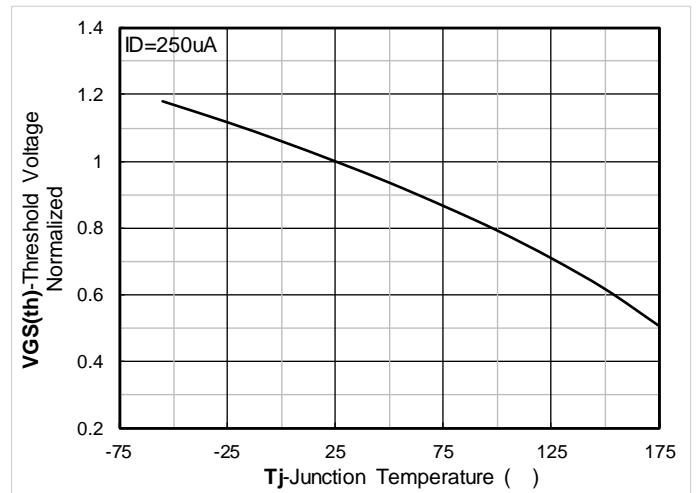


Figure 10. Normalized threshold voltage





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Figure B. Gate Charge Test Circuit & Waveform

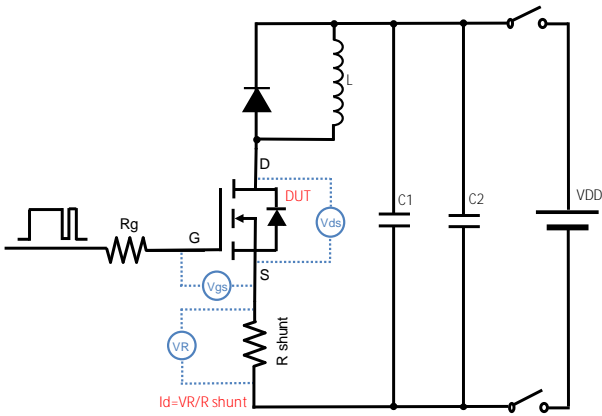


Figure C. Resistive Switching Test Circuit & Waveform

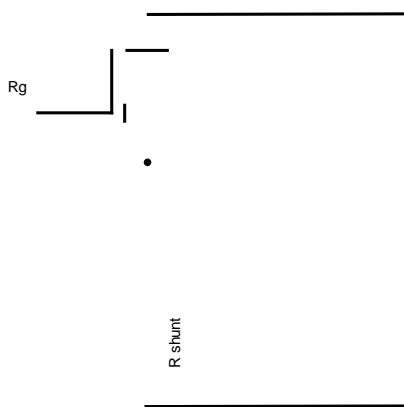
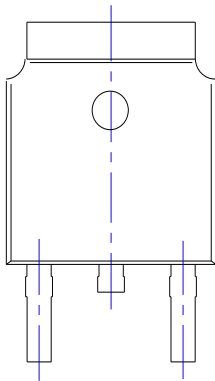


Figure D. Diode Recovery Test Circuit & Waveform



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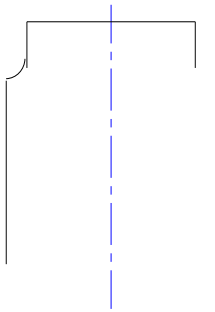
## TO-252-B Package information



TOP VIEW



SIDE VIEW



BOTTOM VIEW

SUGGESTED SOLDER PAD LAYOUT

SYMBOL	DIMENSIONS				
	INCHES				
	MIN.	NOM.			
A1	0.000				
A2	0.087	0.091			
A3	0.035	0.039			
b	0.026	0.030			
c	0.018	0.020			
D	0.256	0.260			
D1					
D2	0.181	0.189			
E	0.390	0.398			
E1	0.236	0.240			

**NOTE:**

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

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